



#### N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

## **Product Summary**

V <sub>SSS</sub>	R <sub>SS(ON)</sub> Max	I <sub>S</sub> T <sub>A</sub> = +25°C
24V	$36m\Omega$ @ $V_{GS} = 4.5V$	5A

## **Features and Benefits**

- Built-in G-S Protection Diode against ESD 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# **Description and Applications**

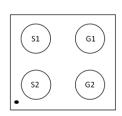
This new generation MOSFET is designed to minimize the on-state resistance (RSS(ON)) and making it ideal for high efficiency power management.

- **Battery Management**
- Load Switch
- **Battery Protection**

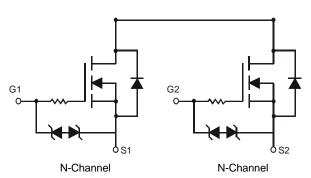
## **Mechanical Data**

- Case: X2-WLB1616-4
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminal Material: SnAgCu Ball
- Weight: 0.0023 grams (Approximate)





Top View



**Equivalent Circuit** 

## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN2036UCB4-7	X2-WLB1616-4	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <a href="https://www.diodes.com/design/support/packaging/diodes-packaging/">https://www.diodes.com/design/support/packaging/diodes-packaging/</a>.
   4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**





VW/WW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		Е		F	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings**

Charac	teristic		Symbol	Value	Unit
Source-Source Voltage			V <sub>SSS</sub>	24	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Source Current @ T <sub>A</sub> = +25°C (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Is	5.0 4.0	А
Pulsed Source Current @ T <sub>A</sub> = +25°C (Notes 5 & 6)			I <sub>SM</sub>	30	А

# Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation, @T <sub>A</sub> = +25°C (Note 5)	$P_{D}$	1.45	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	86.68	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
DFF CHARACTERISTICS (Note 7)									
Source to Source Breakdown Voltage T <sub>J</sub> = +25°C	V <sub>(BR)SS</sub>	24	_	_	V	$I_S = 1mA$ , $V_{GS} = 0V$			
Zero Gate Voltage Source Current T <sub>J</sub> = +25°C	I <sub>SSS</sub>	1	_	1.0	μA	$V_{SS} = 20V$ , $V_{GS} = 0V$			
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{SS} = 0V$			
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.3	V	$V_{SS} = 10V, I_S = 1.0mA$			
Static Source-Source On-Resistance	R <sub>SS(ON)</sub>	20 20.5 21 22 23	29 30 31 33 36	36 37 39 44 52	mΩ	V <sub>GS</sub> = 4.5V, I <sub>S</sub> = 3.0A V <sub>GS</sub> = 4.0V, I <sub>S</sub> = 3.0A V <sub>GS</sub> = 3.7V, I <sub>S</sub> = 3.0A V <sub>GS</sub> = 3.1V, I <sub>S</sub> = 3.0A V <sub>GS</sub> = 2.5V, I <sub>S</sub> = 3.0A			
Forward Transfer Admittance	Y <sub>fs</sub>	_	9.4	_	S	$V_{SS} = 10V, I_S = 3.0A$			
Body Diode Forward Voltage	V <sub>F(S-S)</sub>	1	0.8	1.2	V	$I_F = 3.0A, V_{GS} = 0V$			
DYNAMIC CHARACTERISTICS (Note 8)									
Total Gate Charge	$Q_g$	_	12.6	_	nC	$V_{GS} = 4.5V$ , $V_{SS} = 10V$ , $I_{S} = 6A$			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	183	_	ns				
Turn-On Rise Time	t <sub>R</sub>		278	_	ns	$V_{DD} = 10V$ ,			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	738	_	ns	$R_L = 3.33\Omega$ , $I_S = 3.0A$			
Turn-Off Fall Time	t <sub>F</sub>	_	572	_	ns				

Notes:

- Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
  Repetitive rating, pulse width limited by junction temperature.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.



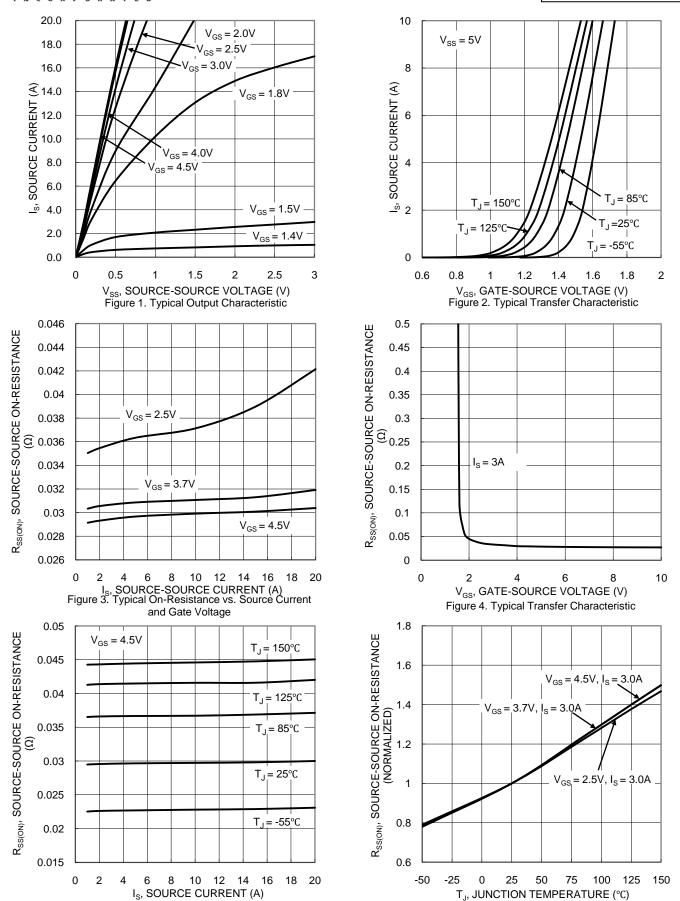


Figure 5. Typical On-Resistance vs. Source Current

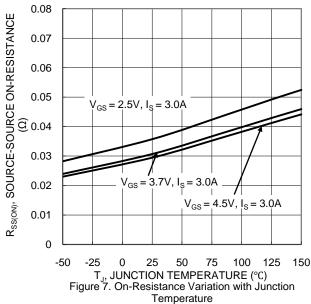
and Junction Temperature

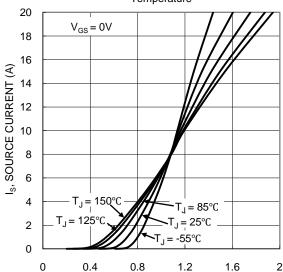
Figure 6. On-Resistance Variation with Junction

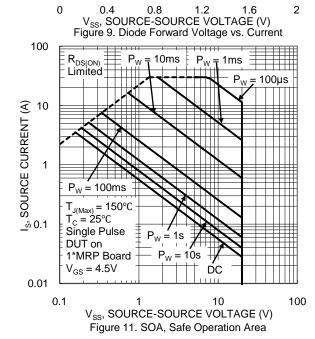
Temperature

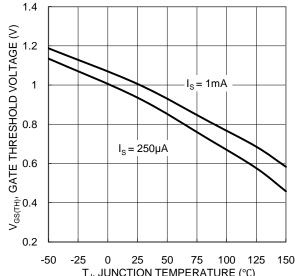




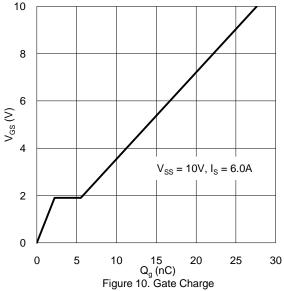








 $T_{\rm J},$  JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature





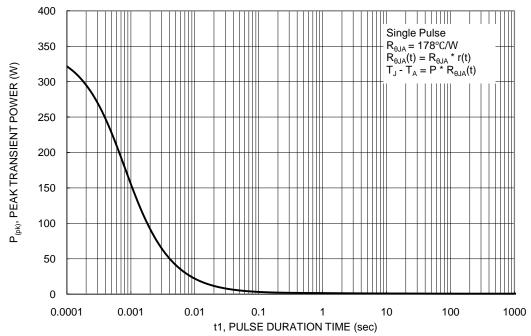
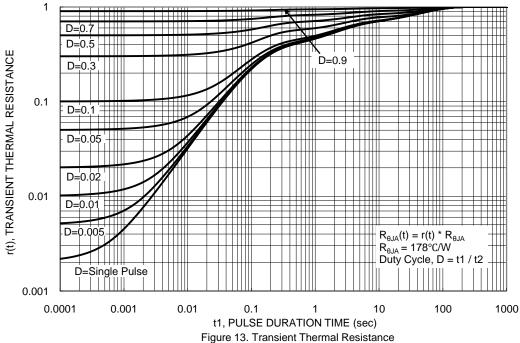


Figure 12. Single Pulse Maximum Power Dissipation

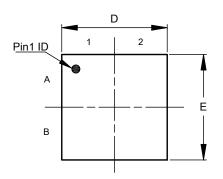


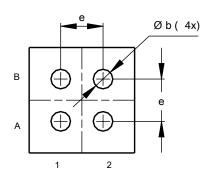


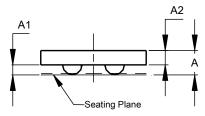
# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X2-WLB1616-4





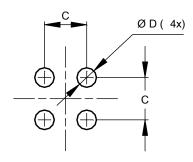


X2-WLB1616-4							
Dim	Min	Тур					
Α		0.40	0.37				
<b>A</b> 1	1	1	0.15				
A2			0.22				
b	0.25	0.35	0.30				
D	1.58	1.66	1.62				
Е	1.58	1.66	1.62				
е	-	-	0.65				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X2-WLB1616-4



Dimensions	Value (in mm)			
С	0.65			
D	0.30			



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